

TWENTIETH ANNUAL



TestConX™

March 3 - 6, 2019

Hilton Phoenix / Mesa Hotel
Mesa, Arizona

Archive

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Testing Challenges for Cu Pillar Wafer by Spring Probe

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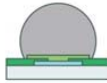

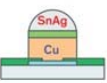
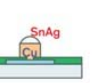
Testing Challenges for Cu Pillar Wafer by Spring Probe

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Cu Pillar Introduction

- WLCSP solder bump has reached its minimum limit in bump size and pitch
- The trend is increasing the number of IO pins in smaller die size at smaller pitch
- Cu Pillar is the next generation bump technology for greater density in smaller pitch
 - Lower cost
 - Ability to mix smaller more flexible shape with thin SnAg cap in finer pitch
 - Superior electrical and thermal performance than that of conventional solder bumps.

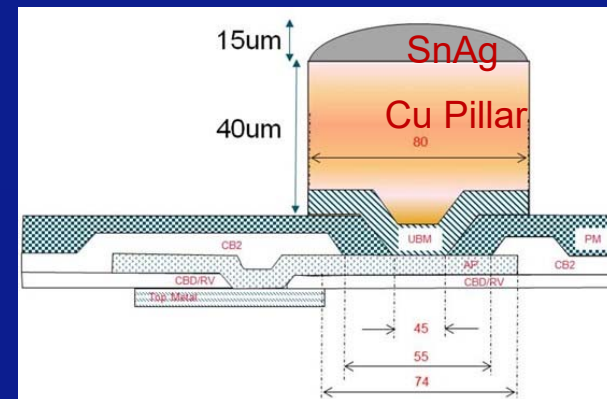
	SnPb C4 Bump	Pb-Free C4 Bump	Cu Pillar + Pb-free Cap	Cu μ -Pillar + Pb-free Cap
Structure				
Diameter	75 – 200 μm	75 – 150 μm	50 – 100 μm	10 – 30 μm

Old Technology Current Technology Next-Generation Technology

Cu Pillar Test Requirement

Probing on Cu Pillar:

- Spring Probes only need to penetrate the thin SnAg Cap for good Cres performance
- Spring Probes should not expose Cu Pillar, to prevent oxidation or create voids, as defects may occur in final SMT reflow process
- Spring Probe Force should not over stress Cu Pillar to avoid damaging the UBM (Under Bump Metallurgy) layer



Existing Cu Pillar WLCSP Test Method by Spring Probe Card

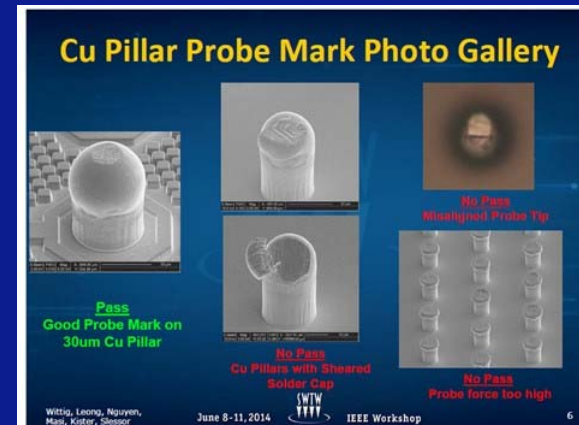


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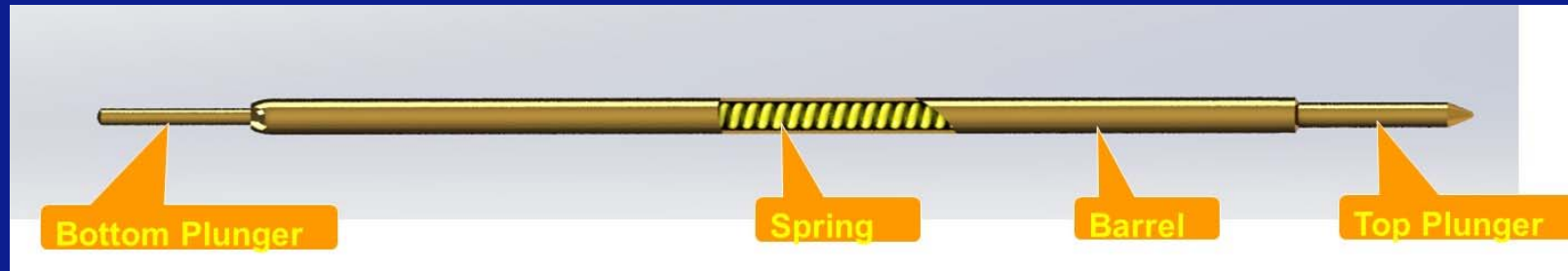


Cu Pillar Test Challenges with Spring Probe

- Probe Head with Spring Probe design must meet mechanical and electrical Cu Pillar test requirements
- Effect of contact mark by Spring Probe on Cu Pillar integrity
- Use FEA and FDR to confirm Spring Probe Design can meet test requirements



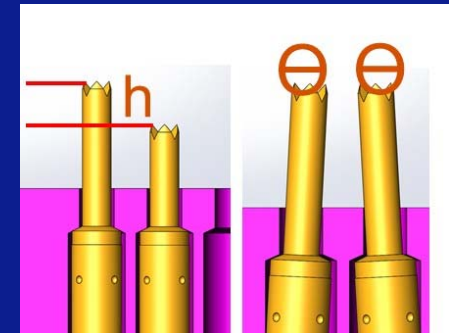
Spring Probe Design Challenge



- Thin cap of SnAg on Cu Pillar is much smaller than conventional solder bump which requires optimized spring probe design.
- Spring Probe must meet all minimum mechanical reliability requirements and at the same time to maintain good Cres performance.

Probe Head Design and Manufacturing Challenges

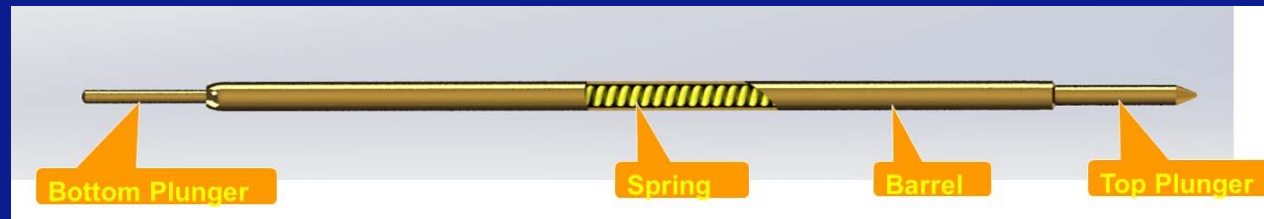
- Spring Probe Tip Tilting and Tip co-planarity
- Spring Probe Tip Material and Geometry
- Probe Head Deflection



- Probe Head design needs to tolerate and consider the effective force of 1st to last touch and tip co-planarity due to manufacturing process.
- Spring Probe Tip material and geometry must optimize to minimize the effect of probe mark on Cu Pillar.

Test Spring Probe Structures

Designed and manufactured 6 new Spring Probes with different spring force and plunger tip geometry



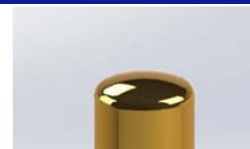
Type A



Type B



Type C

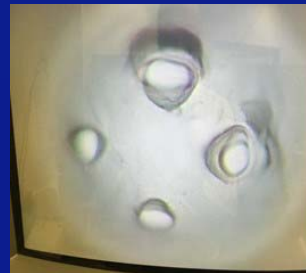


Cu Pillar Prober Test with Spring Probe

Extensive Probe Mark Analysis DOE

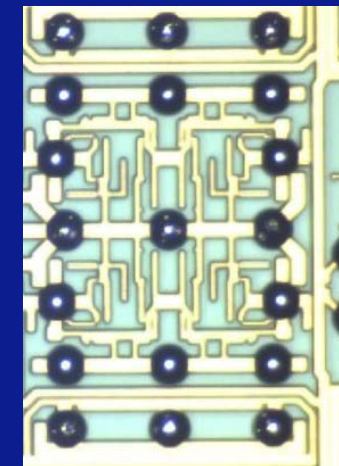
- Cycle 6 Probe Head with 3 different Plunger tip (A, B and C) with 2 different gram force springs on fresh wafer row each time, using Cu Pillar wafer.
- Analyze Probe Mark size and depth after each 1, 3 and 5 touch down, at 100 to 160um of over drive

Example of probing 9
Cu Pillars on one Die
ID# Y33 – X58
5TD at 130um OD



Probe Mark Depth

UADRA-CHEK 200	
Probe Dist. mm +	
X	0.0000
Y	0.0000
Z	0.0095
Recall Create Const	



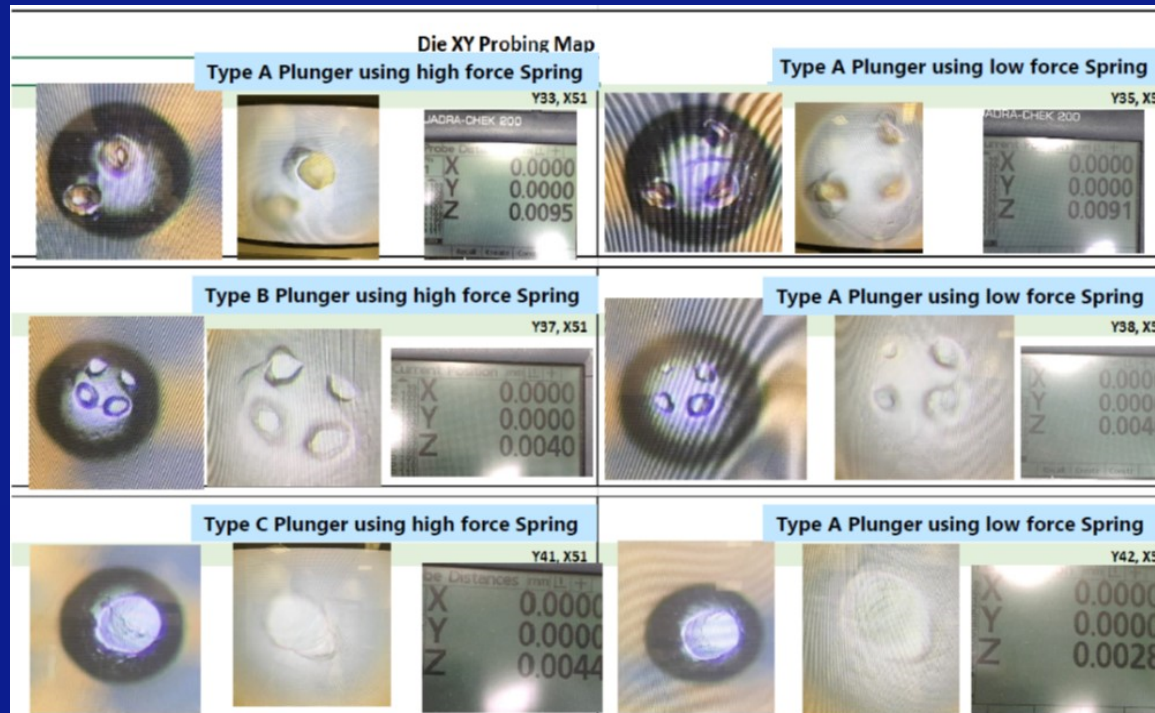
Testing Challenges for Cu Pillar Wafer by Spring Probe

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Cu Pillar Prober Test with Spring Probe

Failed Probe
Mark Depth



Heavy Probe
Mark

Heavy Probe
Mark

Okay

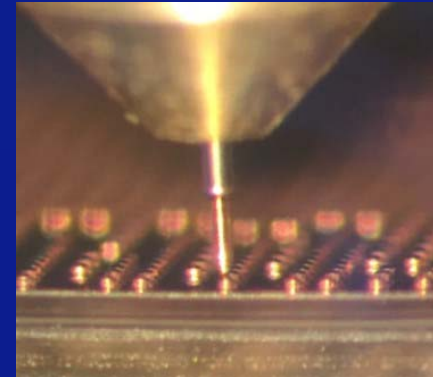
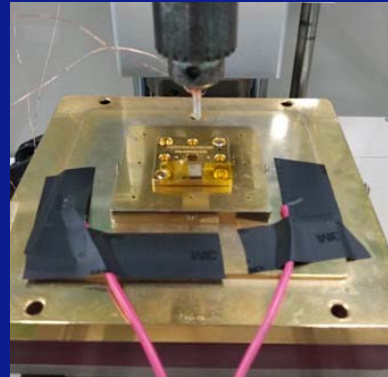
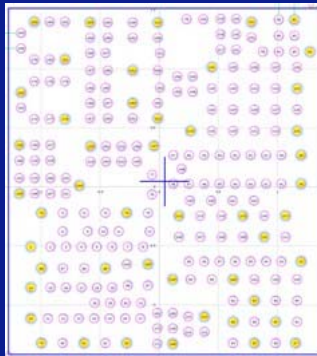
Heavy Probe
Mark

Okay

Cu Pillar Single Die Test with Spring Probes

Test Setup

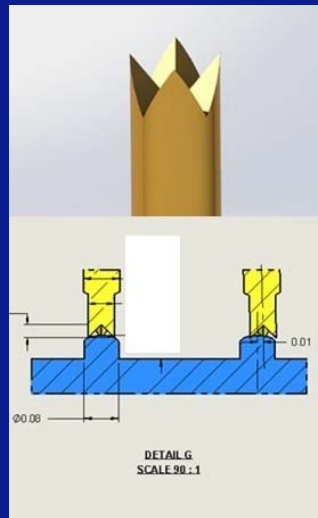
- Designed a test fixture to align with single die and use FDR Tester and short some Cu Pillar to FDR Tester GND (Sense) Channel.
- Designed FDR Pin Adapter to hold Spring Probe (in preload condition) and connect the plunger to the FDR Force Channel.
- Align Cu Pillar with each type of Spring Probe and obtain FDR to highlighted Cu Pillars.
- Analyze Probe Mark and Cres vs Deflection vs Force for each type of spring probe.



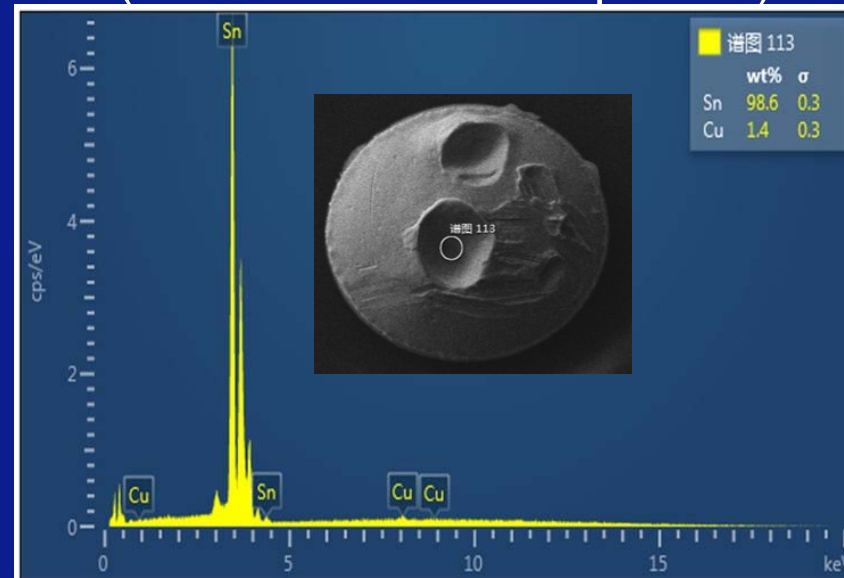
Testing Challenges for Cu Pillar Wafer by Spring Probe

Probe Mark Analysis

Type A top plunger

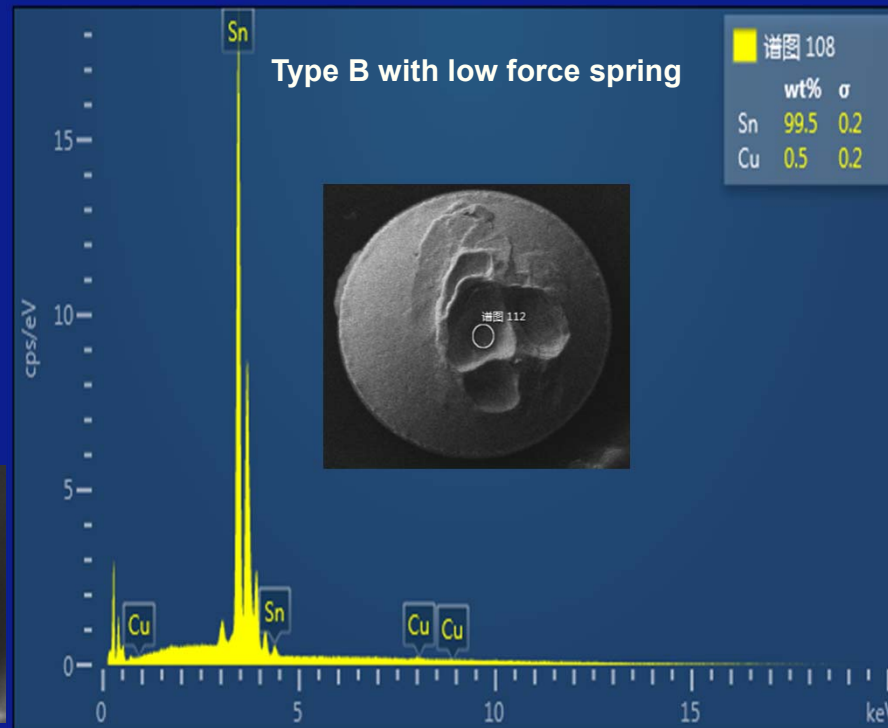
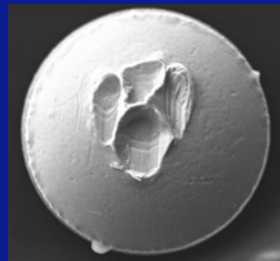
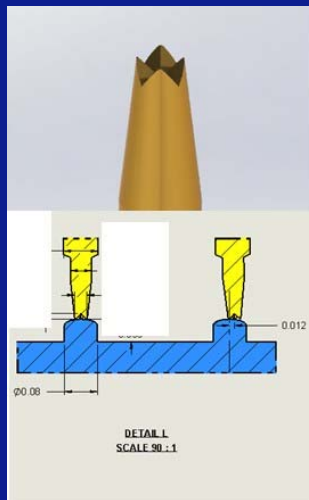


Type A with high force spring
(Failed due to Cu exposure)



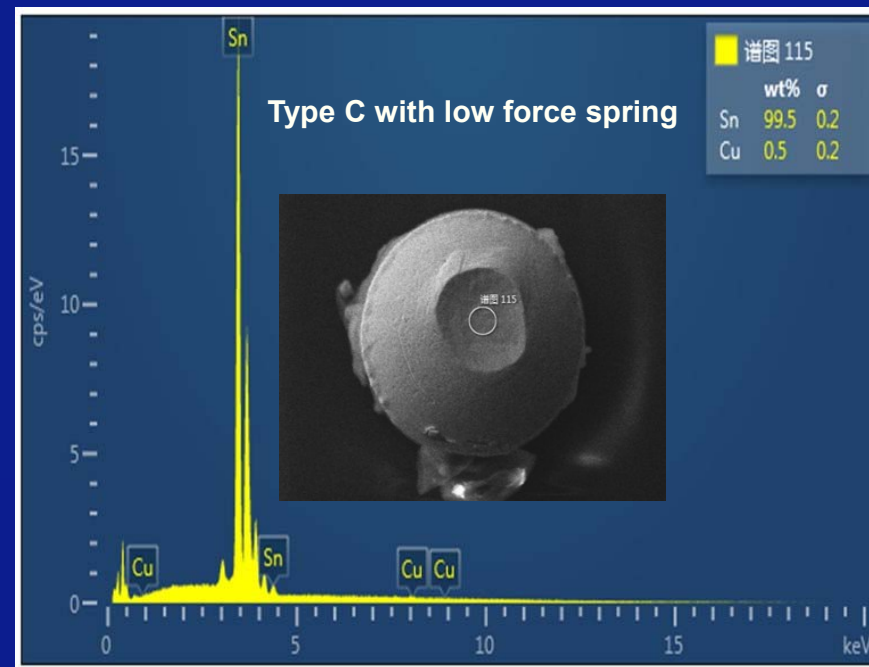
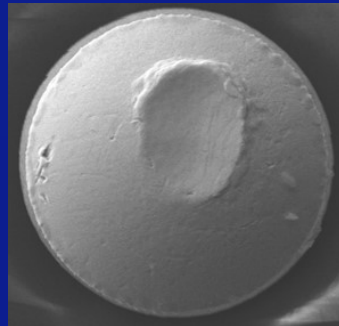
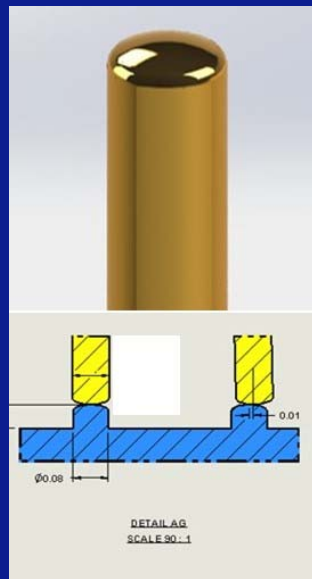
Probe Mark Analysis

Type B top plunger

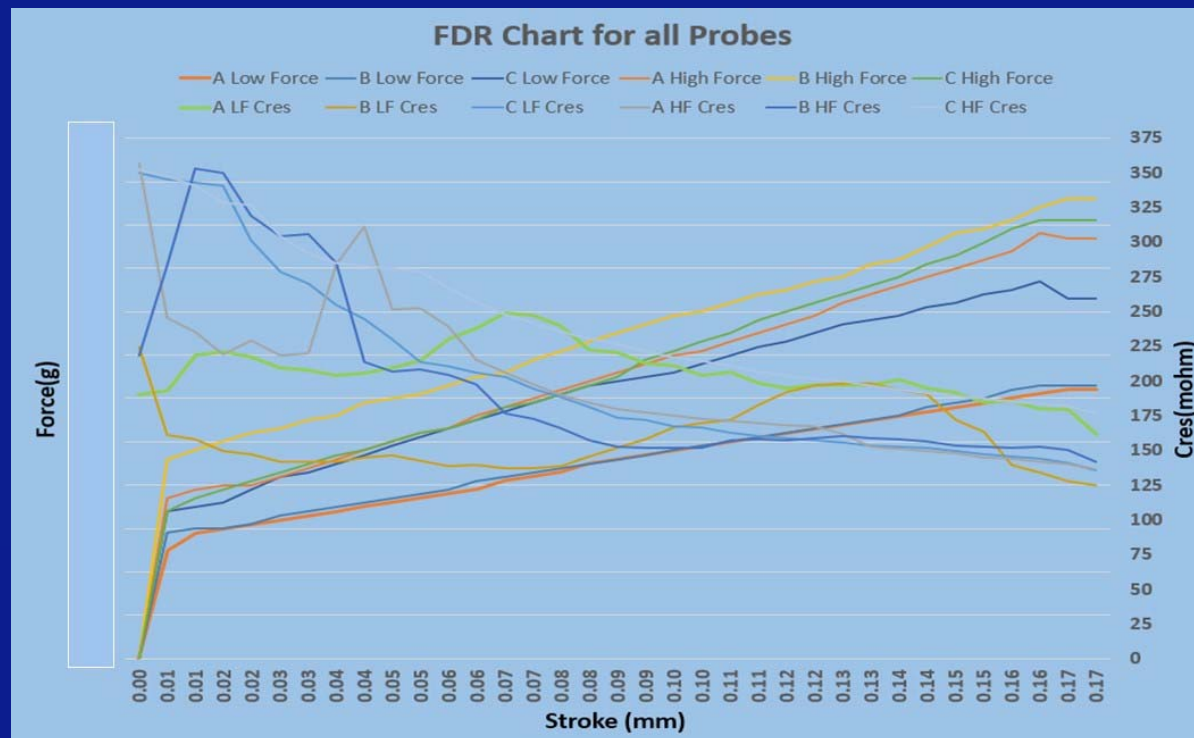


Probe Mark Analysis



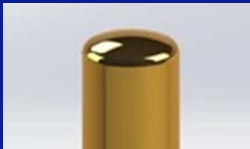
Type C top plunger



FDR Chart For All Probes



FDR Test Result Comparison

Spring Probe Tip Type		Cres (mOhm)
Type A with High and Low Spring Force		179.9
		154.8
Type B with High and Low Spring Force		152.4
		128.4
Type C with High and Low Spring Force		183.8
		142.4

Recommendation and Summary



- Type A causing deep mark $> 9 \mu\text{m}$ too close to expose Cu and cause defect.



- Type B with optimized force is showing good Cres, acceptable probe mark, and will be released to production to evaluate life verse yield and performance.



- Type C with optimized force is showing good Cres, acceptable probe mark, and will be released to production to evaluate life verse yield and performance.

**** 2 PH with Type B and C will be released in HVM this spring for field validation.